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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Application Serial No
Filing Date June 4, 2001
Inventor
Assignee Micron Technology, Inc.
Group Art Unit
Examiner E. Ortiz
Attorney's Docket No MI22-1741
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects,
and Wordline, Transistor Gate, and Conductive Interconnect Structures

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - - See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Date: / 2 - 2 / - 0

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No	. 09/332,27
Priority Filing Date	June 11, 1999
Inventor Klaus Florian S	chuegraf et al
Assignee Micron Te	chnology, Inc
Priority Group Art Unit	
Priority Examiner	E. Le
Attorney's Docket No	Mi22-174
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive	Interconnects
and Wordline Transistor Gate, and Conductive Interconnect Struct	

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, copending application of the above-identified application. The above-identified application is a divisional of co-pending Application Serial No. 09/332,271, filed on June 11, 1999. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 6-4-01

Attorney:

D. Brent Kenady Reg. No. 40,045

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MI22-1741 APPLICANT Klaus Florian Schuegraf et al. TECHNOLOGY

LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)

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